# Supporting Information

## Reduced Contact Resistance in Inkjet Printed High-Performance Amorphous Indium Gallium Zinc Oxide Transistors

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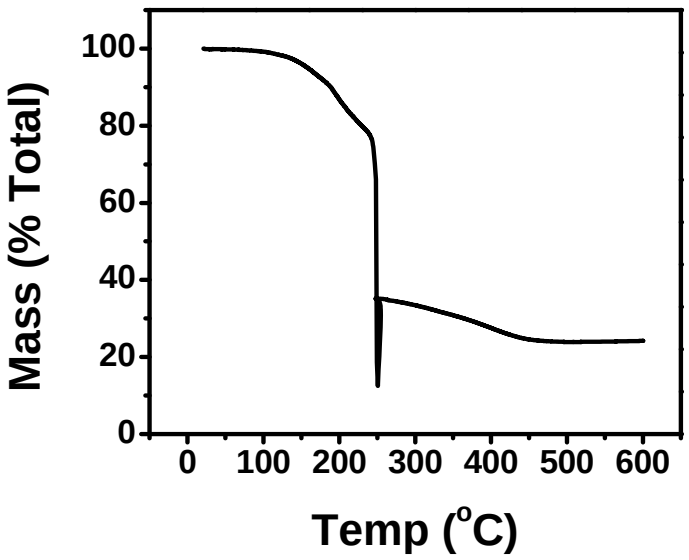


**Figure S1.** Thermogravimetric analysis (TGA) of the a-IGZO sol-gel precursor showing abrupt mass loss at 240 °C.

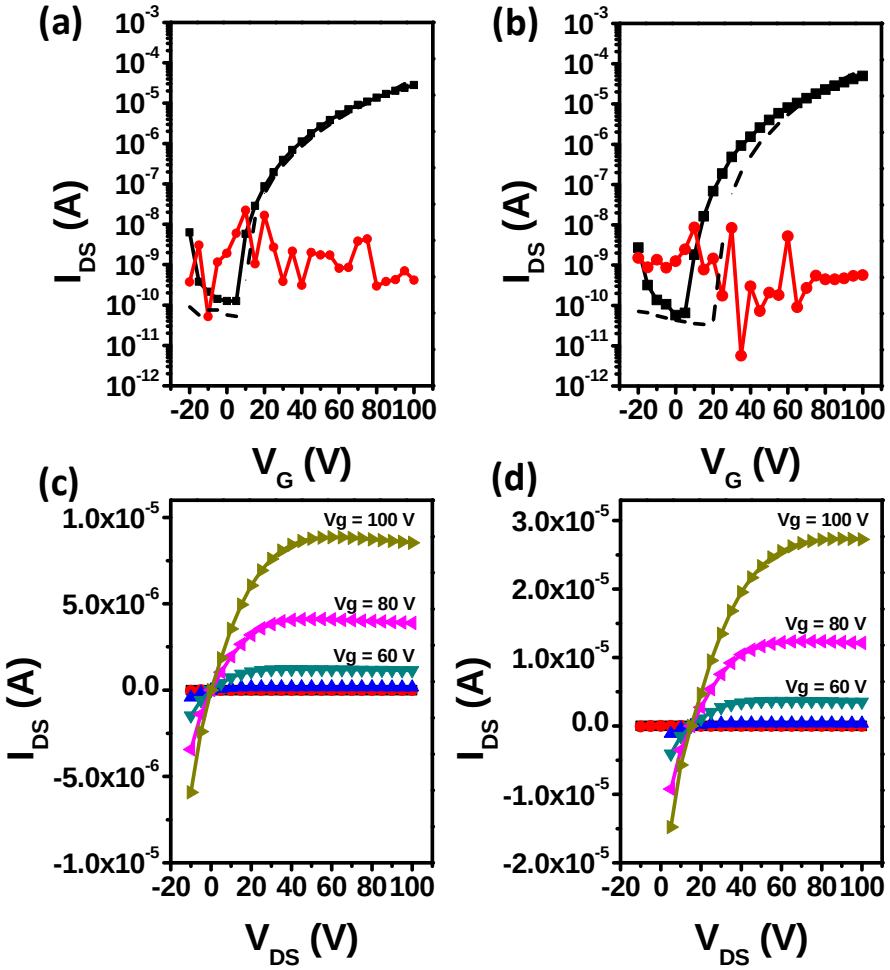


**Figure S2.** Typical transfer (a,b) and output (c,d) characteristics for top-contact (a,c) and bottom-contact (b,d) printed a-IGZO TFTs annealed at 300 °C. The transfer plots show very low gate leakage (red).